

WN3S10S200CXT

Dual power Schottky diode

Rev.01 - 15 November 2023

Product data sheet

1. General description

Dual common cathode power Schottky diode in TO220F plastic package



2. Features and benefits

- High junction temperature up to 175°C
- · Low forward voltage drop, negligible switching losses
- High efficiency

3. Applications

- DC to DC converters
- Freewheeling diode
- OR-ing diode
- Switched mode power supply rectifier

4. Quick reference data

Symbol	Parameter	Conditions	Notes	Values		Unit	
		Conditions	Notes		values		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage				200		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3		5		А	
$I_{O(AV)}$	average output current	δ = 0.5 ; square-wave pulse; both diodes conducting		10		A	
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	0.83	0.93	V
I _R	reverse current	V _R = 200 V; T _i = 25 °C; per diode; <u>Fig. 7</u>		-	0.03	5	μA

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	К	cathode		
3	A2	anode 2		K sym125
mb	n.c.	mounting base; isolated		5,

6. Ordering information

Table 3. Ordering information									
Type number	Package	Orderable part number	J	Small packing		Package			
	name		method	quantity	version	issue date			
WN3S10S200CXT	TO220F	WN3S10S200CXTQ	Tube	50	SOT186A	14-Nov-2013			

7. Marking

Table 4. Marking codes						
Type number	Marking codes					
WN3S10S200CXT	WN3S10S 200CXT					

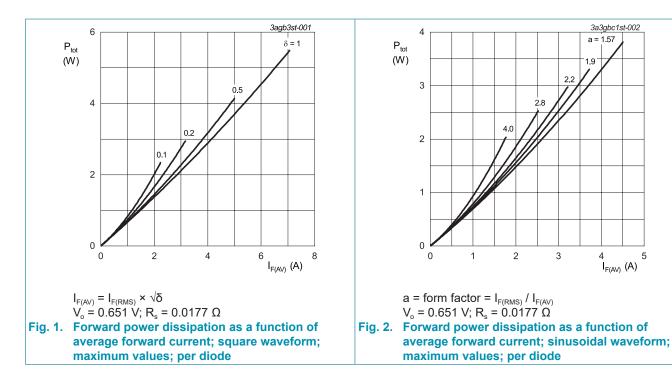
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

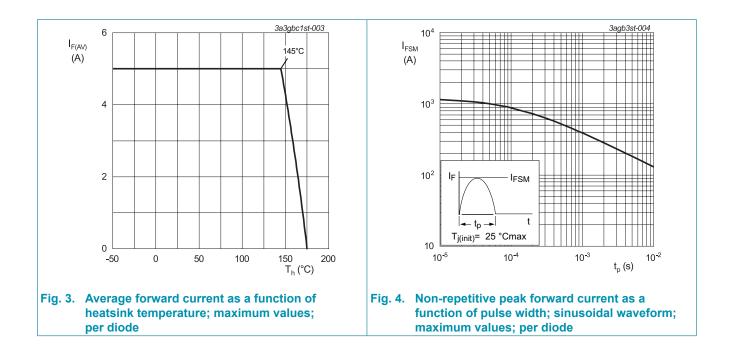
Symbol	Parameter	Conditions	Notes	Values	Unit
V _{RRM}	repetitive peak reverse voltage			200	V
V _{RWM}	crest working reverse voltage			200	V
V _R	reverse voltage	DC		200	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3		5	A
I _{O(AV)}	average output current	δ = 0.5 ; square-wave pulse; both diodes conducting		10	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>		130	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		143	A
T _{stg}	storage temperature			-40 to 175	°C
T _j	junction temperature		[1]	-40 to 175	°C

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient: $dP_{tot}/dT_j < 1/R_{th(j-a)}$



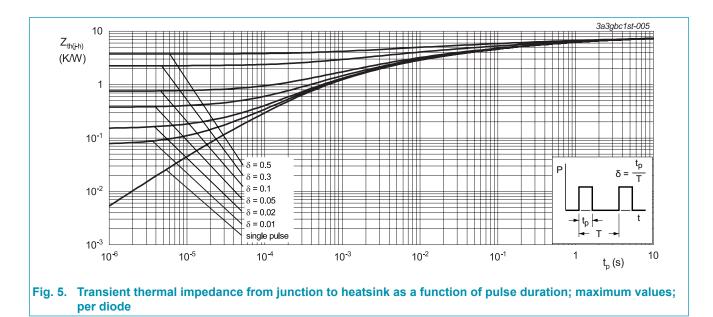
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9. Thermal characteristics

Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-h)}}$	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5		-	-	7.3	K/W
	heatsink	with heatsink compound; both diodes conducting		-	-	5.2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



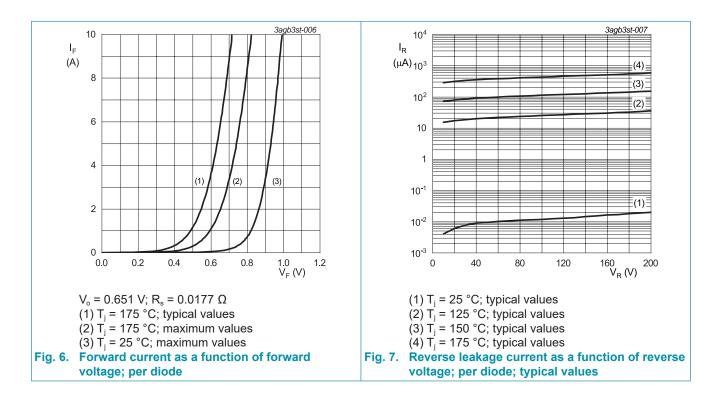
10. Isolation characteristics

Table 7. Isolation characteristics

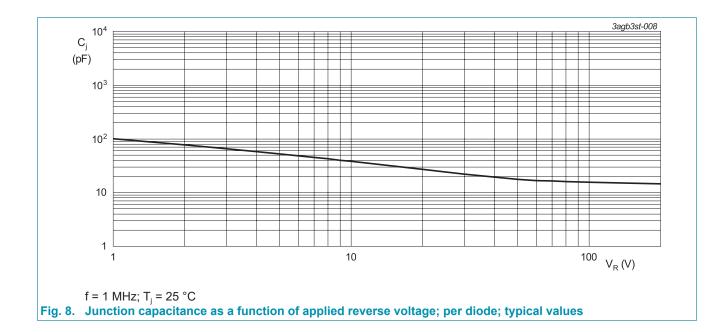
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; T _h = 25 °C; RH \leq 65 %		-	-	2500	V

11. Characteristics

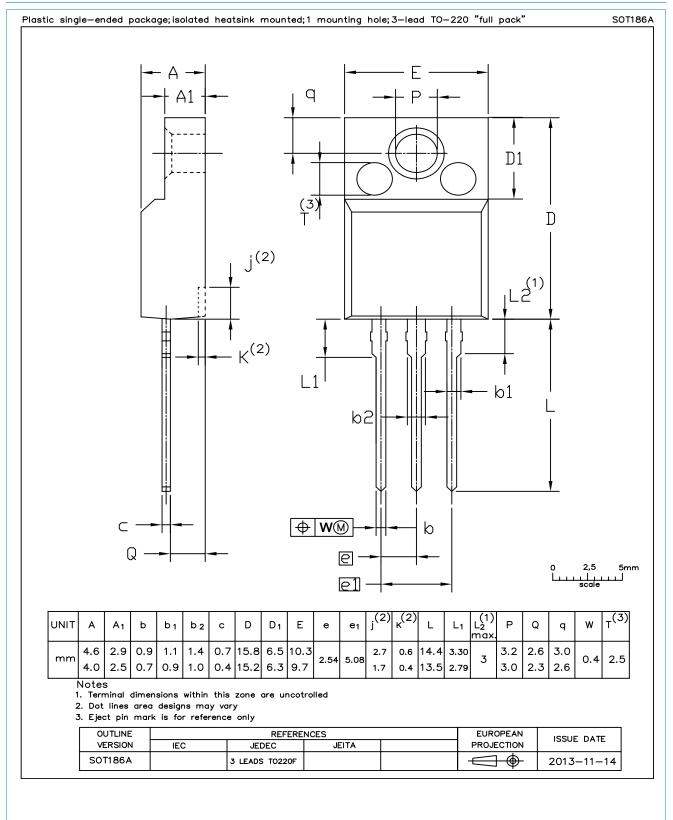
Table 8. Characteristics							
Symbol	Parameter	Conditions	Notes	Min	Тур	Мах	Unit
Static characteristics							
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	0.83	0.93	V
		$I_F = 5 \text{ A}; T_j = 125 \text{ °C}; \text{ per diode}$		-	0.70	-	V
		I _F = 5 A; T _j = 175 °C; per diode; <u>Fig. 6</u>		-	0.64	0.74	V
I _R	reverse current	V_{R} = 200 V; T _j = 25 °C; per diode; <u>Fig. 7</u>		-	0.03	5	μA
		V_R = 200 V; T _j = 125 °C; per diode; <u>Fig. 7</u>		-	0.04	-	mA



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12. Package outline



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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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